Amendments to the Specification:

Please add, beginning at page 6, between lines 17 and 18, the following new paragraph:

Thus, the transistor of the present invention can be operated by the following method: applying a first voltage potential to a base of a transistor, the base being formed by a base well of a first conductivity type; applying a second voltage potential to a first electrode of a transistor, the first electrode being an outer and inner conductive regions of a second conductivity type formed in the base well in a substantially concentric manner and connected to a common metal region; and applying a third voltage potential to a second electrode of a transistor, the second electrode being an intermediate conductive region of the second conductivity type formed in the base well in a substantially concentric manner with respect to the inner conductive region.

Please add, beginning at page 7, between lines 3 and 4, the following new paragraph:

Thus, the transistors of the present invention can be operated by the following method: applying a first voltage potential to the base of a first transistor, said base being formed by a base well of a first conductivity type; applying a second voltage potential to a first electrode of the first transistor, said electrode being connected to an inner conductive region of a second conductivity type, having a substantially circular shape formed within the base well; applying a third voltage potential to a second electrode of the first transistor, said electrode being connected to an intermediate conductive region of a second conductivity type, having a substantially annular shape and surrounding the inner conductive region in a concentric manner, thereby obtaining a first current gain; applying a fourth voltage potential to a first electrode of the second transistor, said electrode being connected to an outer conductive region of a second conductive type, having a substantially annular shape and surrounding the intermediate conductive region in a concentric manner; and applying a fifth voltage potential to a second electrode of the second transistor, said electrode being connected to the intermediate conductive region, thereby obtaining a second current gain.